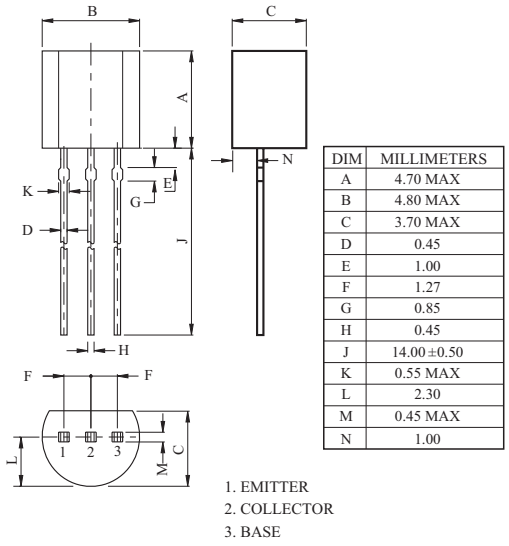
KTC3203A

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT APPLICATION.

FEATURES

· Complementary to KTA1271A



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00 ±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. COLLECTOR
3. BASE

TO-92 (F)

MAXIMUM RATING (Ta=25℃)

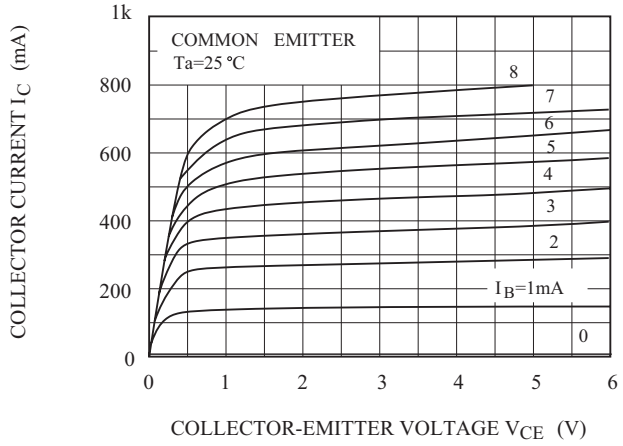
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	℃
Operating Temperature	T_{opr}	-40 85	℃
Storage Temperature Range	T_{stg}	-55 150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

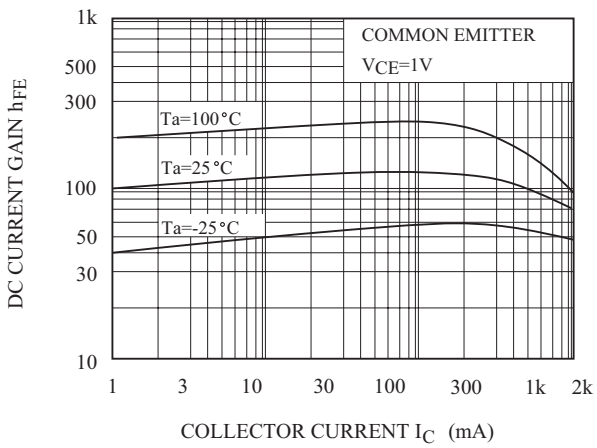
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=35V, I_E=0	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	30	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=1V, I_C=100mA	100	-	320	
	h_{FE}(2)	V_{CE}=1V, I_C=700mA	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=20mA	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=1V, I_C=10mA	0.5	-	0.8	V
Transition Frequency	f_T	V_{CE}=5V, I_C=10mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	19	-	pF

Note : h_{FE}(1) Classification 0:100 200, Y:160 320

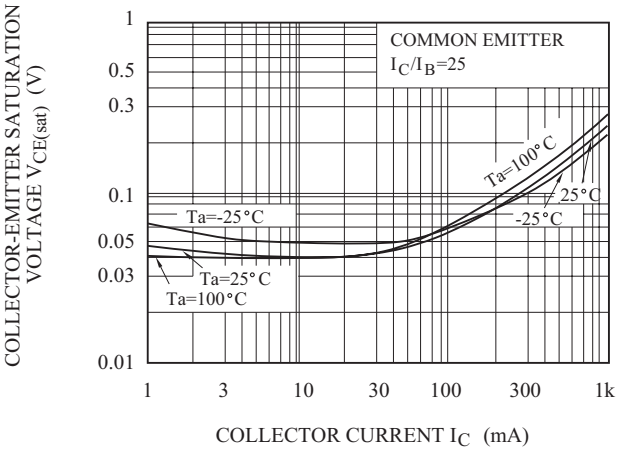
I_C - V_{CE}



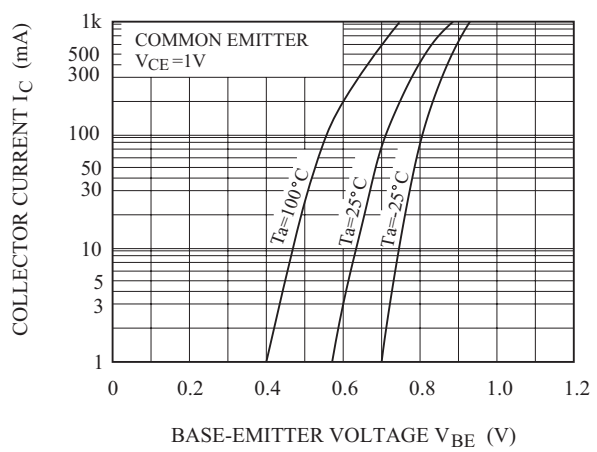
h_{FE} - I_C



$V_{CE(sat)}$ - I_C



I_C - V_{BE}



Pc - Ta

